鼎德丰
DING DE FENG

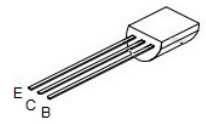
PNP Silicon Transistor

2SB1116A

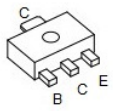
- **Complementary to：2SD1616A**
- **Package: TO-92/SOT-89**

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	-120		V
Collector-emitter voltage	BV_{CEO}	-60		V
Emitter-base voltage	BV_{EBO}	-6		V
Collector current	I_{CM}	-1		A
Collector Power Dissipation	P_C	TO-90	750	mW
		SOT-89	500	
Junction Temperature	Tj	150		℃
Storage Temperature	Tstg	-55～+150		℃



TO-92



SOT-89

Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-10μA，I_E=0	-120			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-2mA，I_B=0	-60			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-10μA，I_C=0	-6			V
collector-base cut-off current	I_{CBO}	V_{CB}=-120V，I_E=0			-0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=-6V，I_C=0			-0.1	μA
DC current gain	H_{FE}	V_{CE}=-2V，I_B=-100mA	135		600	
	H_{FE1}	V_{CE}=-2V，I_B=-1A	80			
collector-emitter saturation voltage	V_{CESAT}	I_C=-1A，I_B=-50mA			-0.3	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=-1A，I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}=-2V，I_B=-100mA	100			MHz

Classification of H_{FE}

Rank	L	K	U
Range	135-270	200-400	300-600